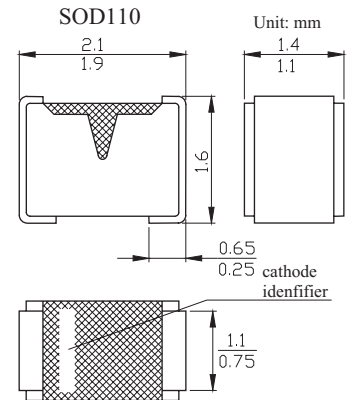


Schottky barrier diode

BAT254

■ Features

- Low forward voltage
- Guard ring protected
- Very small ceramic SMD package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			30	V
Continuous forward current	I_F			200	mA
Repetitive peak forward current	I_{FSM}	$t_p \leq 1\text{s}; \delta \leq 0.5$		300	mA
Non-repetitive peak forward current	I_{FSM}	$t_p < 1\text{s}$		600	mA
Storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
Junction temperature	T_j			125	$^\circ\text{C}$
Operating ambient temperature	T_{amb}		-65	+125	$^\circ\text{C}$

Schottky barrier diode

BAT254

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Max	Unit
forward voltage	V _F	I _F = 0.1 mA	240	mV
		I _F = 1 mA	320	
		I _F = 10 mA	400	
		I _F = 30 mA	500	
		I _F = 100 mA	800	
reverse current	I _R	V _R = 25 V, note 1	2	μ A
reverse recovery time	t _{rr}	when switched from I _F = 10 mA to I _R = 10 mA; R _L = 100 Ω measured at I _R = 1 mA	5	ns
diode capacitance	C _d	f = 1 MHz; V _R = 1 V;	10	pF
thermal resistance from junction to ambient	R _{th j-a}	note 2	315	K/W

Note

1.Pulsed test: t_p = 300 μ s, δ = 0.02.

2.Refer to SOD110 standard mounting conditions.

■ Marking

Marking	L4
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